





#### 180V NPN MEDIUM POWER HIGH GAIN TRANSISTOR IN SOT223

#### **Features**

- BV<sub>CEO</sub> > 180V
- I<sub>C</sub> = 0.5A Continuous Current
- hFE > 500 for High Gain @ 0.1A
- Very Low Saturation Voltage
- Complementary PNP Type: FZT795A
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound;
   UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.112 grams (Approximate)

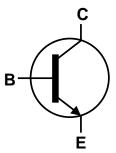
### **Applications**

- Darlington Replacement
- · Relay and Solenoid Driver

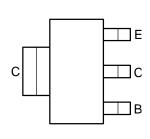




Top View



Device Symbol



Top View Pin-Out

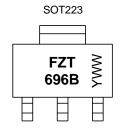
#### Ordering Information (Note 4)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FZT696BTA	AEC-Q101	FZT696B	7	12	1,000
FZT696BTC	AEC-Q101	FZT696B	13	12	4,000

Notes:

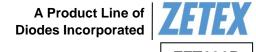
- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

#### **Marking Information**



FZT 696B = Product Type Marking Code YWW = Date Code Marking Y or  $\overline{Y}$  = Last Digit of Year (ex: 5= 2015) WW or  $\overline{W}W$  = Week Code (01~53)





FZT696B

### Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	180	V
Collector-Emitter Voltage	$V_{CEO}$	180	V
Emitter-Base Voltage	$V_{EBO}$	7	V
Continuous Collector Current	lc	0.5	Α
Peak Pulse Current	I <sub>CM</sub>	1	Α

#### Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		3		
Power Dissipation	(Note 6)	Б	2	W	
Power Dissipation	(Note 7)	$P_{D}$	1.6		
	(Note 8)		1.2		
	(Note 5)		41.7		
Thermal Resistance, Junction to Ambient	(Note 6)	D	62.5		
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{ hetaJA}$	78.1	°C/W	
	(Note 8)		104	1	
Thermal Resistance Junction to Lead (Note 9)		$R_{ hetaJL}$	12.9		
Operating and Storage Temperature Range	$T_{J}, T_{STG}$	-55 to +150	°C		

### ESD Ratings (Note 10)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

- 5. For a device mounted with the collector lead on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

- 6. Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.

  7. Same as Note 5, except the device is mounted on 25mm x 25mm 1oz copper.

  8. Same as Note 5, except the device is mounted on minimum recommended pad layout.

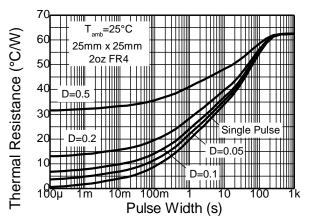
  9. Thermal resistance from junction to solder-point (at the end of the collector lead).

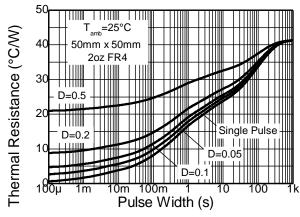
  10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.





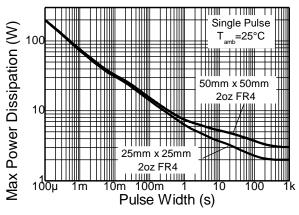
# **Thermal Characteristics and Derating Information**

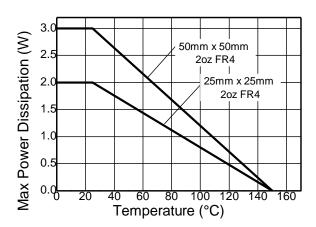




**Transient Thermal Impedance** 

**Transient Thermal Impedance** 





**Pulse Power Dissipation** 

**Derating Curve** 





### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	180	_	_	V	$I_{C} = 100 \mu A$
Collector-Emitter Breakdown Voltage (Note 11)	BV <sub>CEO</sub>	180	_	_	V	$I_C = 10mA$
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	7	_	_	V	$I_E = 100 \mu A$
Collector-Base Cut-Off Current	I <sub>CBO</sub>	_	_	100	nA	V <sub>CB</sub> = 140V
Emitter Cut-Off Current	I <sub>EBO</sub>	_	_	100	nA	V <sub>EB</sub> = 4V
DC Current Gain (Note 11)	h <sub>FE</sub>	500 150	_	_		$I_C = 100 \text{mA}, V_{CE} = 5 \text{V}$ $I_C = 200 \text{mA}, V_{CE} = 5 \text{V}$
Collector-Emitter Saturation Voltage (Note 11)	V <sub>CE(sat)</sub>	_ _ _ _	_ _ _	200 200 250	mV	I <sub>C</sub> = 50mA, I <sub>B</sub> = 0.5mA I <sub>C</sub> = 100mA, I <sub>B</sub> = 2mA I <sub>C</sub> = 200mA, I <sub>B</sub> = 5mA
Base-Emitter Saturation Voltage (Note 11)	V <sub>BE(sat)</sub>	_	_	0.9	V	$I_C = 200 \text{mA}, I_B = 50 \text{mA}$
Base-Emitter Turn-On Voltage (Note 11)	V <sub>BE(on)</sub>	_	_	0.9	V	$I_C = 200 \text{mA}, V_{CE} = 5 \text{V}$
Input Capacitance	C <sub>ibo</sub>	_	200	_	pF	$V_{EB} = 0.5V, f = 1MHz$
Output Capacitance	C <sub>obo</sub>	_	6	_	pF	$V_{CB} = 10V$ , $f = 1MHz$
Current Gain-Bandwidth Product	f⊤	130	_	_	MHz	V <sub>CE</sub> = 5V, I <sub>C</sub> = 50mA, f=50MHz
Turn-On Time	t <sub>on</sub>	_	80	_	ns	V <sub>CC</sub> = 50V, I <sub>C</sub> = 100mA
Turn-Off Time	t <sub>off</sub>	_	4400	_	ns	$I_{B1} = -I_{B2} = 10mA$

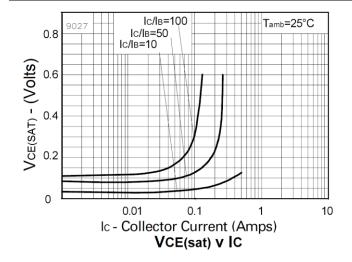
Note:

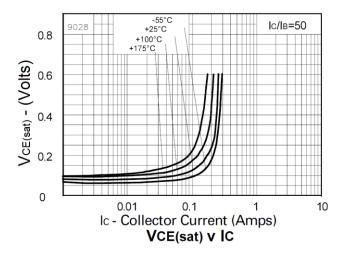
11. Measured under pulsed conditions. Pulse width  $\leq$  300  $\mu s.$  Duty cycle  $\leq$  2%.

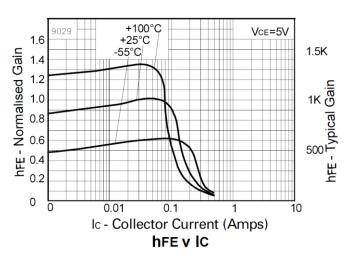


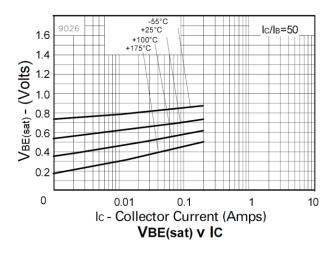


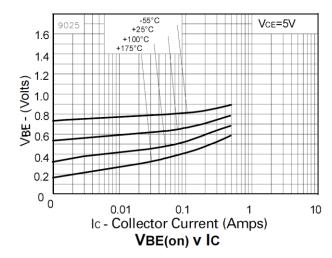
## Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)







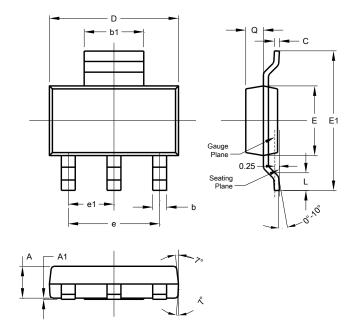






### **Package Outline Dimensions**

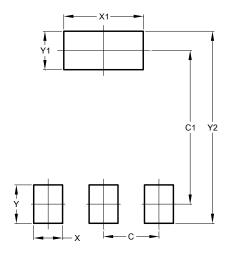
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223				
Dim	Min	Max	Тур	
Α	1.55	1.65	1.60	
A1	0.010	0.15	0.05	
b	0.60	0.80	0.70	
b1	2.90	3.10	3.00	
С	0.20	0.30	0.25	
D	6.45	6.55	6.50	
Е	3.45	3.55	3.50	
E1	6.90	7.10	7.00	
е	-	-	4.60	
e1	-	-	2.30	
L	0.85	1.05	0.95	
Ø	0.84	0.94	0.89	
All Dimensions in mm				

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Υ	1.60
Y1	1.60
Y2	8.00

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.





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